Toohong

PMEG045V100EPD

45 V, 10 A low VF MEGA Schottky barrier rectifier

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a CFP15 (SOT1289) power and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Average forward current: $I_{F(AV)} \leq 10$ A
- Reverse voltage: $V_R \leq 45$ V
- Extremely low forward voltage
- High power capability due to clip-bonding technology and heat sink
- Small and thin SMD power plastic package, typical height 0.78 mm
- AEC-Q101 qualified

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Freewheeling application
- Reverse polarity protection
- Low power consumption application

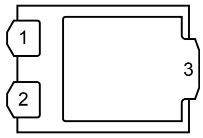
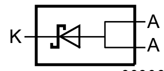
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$I_{F(AV)}$	average forward current	$\delta = 0.5$; f = 20 kHz; $T_{sp} \leq 160$ °C; square wave		-	-	10	A
V_R	reverse voltage	$T_j = 25$ °C		-	-	45	V
V_F	forward voltage	$I_F = 10$ A; $t_p \leq 300$ μs; $\delta \leq 0.02$; $T_j = 25$ °C; pulsed		-	420	490	mV
I_R	reverse current	$V_R = 10$ V; $t_p \leq 3$ ms; $\delta \leq 0.3$; $T_j = 25$ °C; pulsed		-	20	50	μA
		$V_R = 45$ V; $t_p \leq 3$ ms; $\delta \leq 0.3$; $T_j = 25$ °C; pulsed		-	250	600	μA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A	anode	 **CFP15 (SOT1289)**	 aaa-009063
2	A	anode		
3	K	cathode		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG045V100EPD	CFP15	plastic, thermal enhanced ultra thin SMD package; 3 leads; body: 5.8 x 4.3 x 0.78 mm	SOT1289

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG045V100EPD	045V 100E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage	T_j = 25 °C		-	45	V
I_F	forward current	T_{sp} = 155 °C; δ = 1		-	14	A
$I_{F(AV)}$	average forward current	δ = 0.5; f = 20 kHz; T_{sp} ≤ 160 °C; square wave		-	10	A
I_{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	210	A
P_{tot}	total power dissipation	T_{amb} ≤ 25 °C	[1]	-	1.66	W
			[2]	-	2.15	W
			[3]	-	3.75	W
T_j	junction temperature			-	175	°C
T_{amb}	ambient temperature			-55	175	°C

Symbol	Parameter	Conditions		Min	Max	Unit
T_{stg}	storage temperature			-65	175	°C

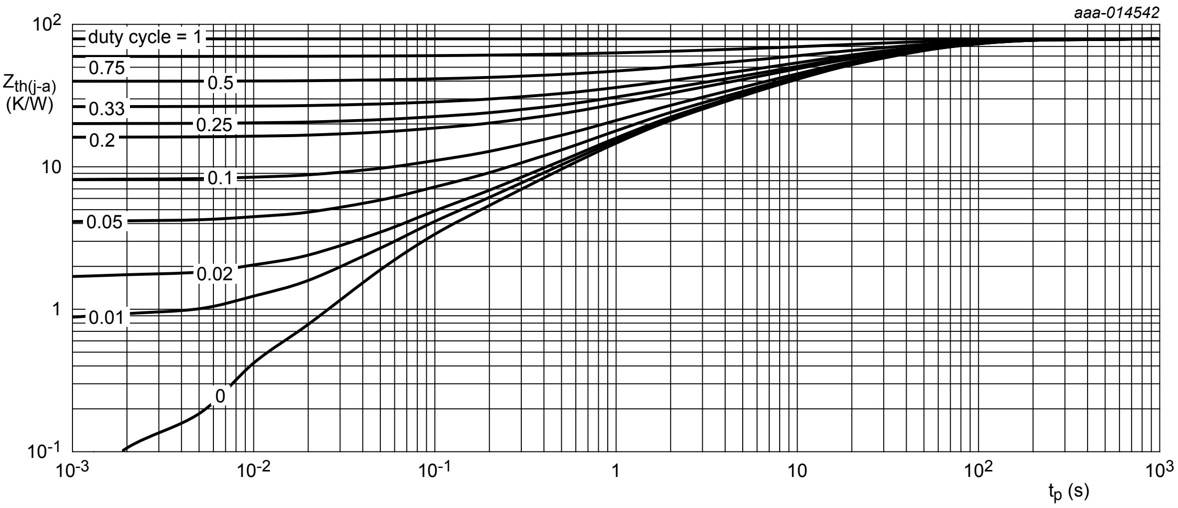
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2.
[3] Device mounted on a ceramic Printed-Circuit Board (PCB), Al_2O_3, standard footprint.

9. Thermal characteristics

Table 6. Thermal characteristics

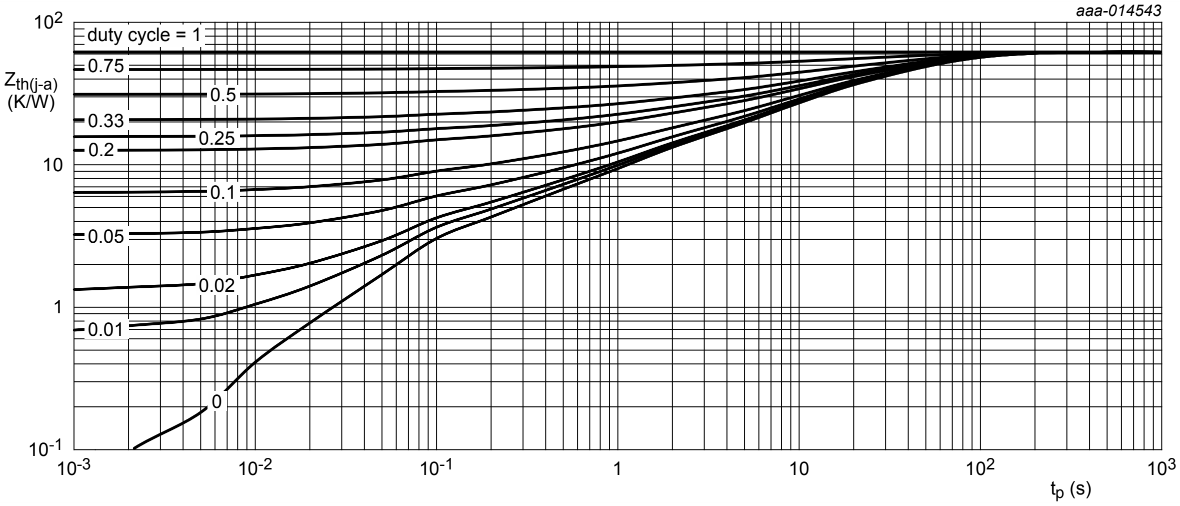
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	-	90	K/W
			[1][3]	-	-	70	K/W
			[1][4]	-	-	40	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[5]	-	-	3	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2.
[4] Device mounted on a ceramic PCB, Al_2O_3, standard footprint.
[5] Soldering point of cathode tab.



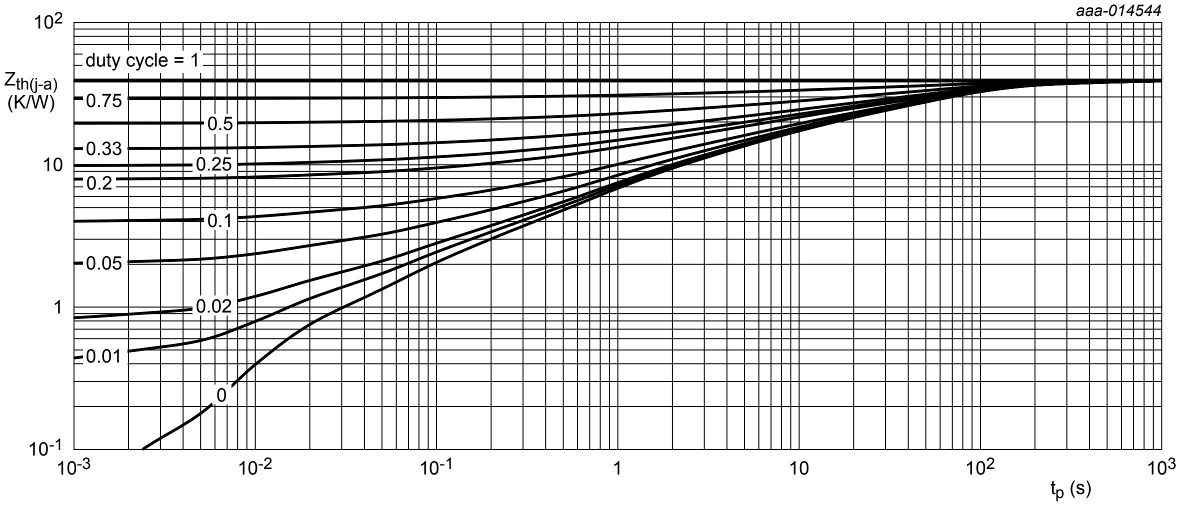
FR4 PCB, standard footprint

Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm^2

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



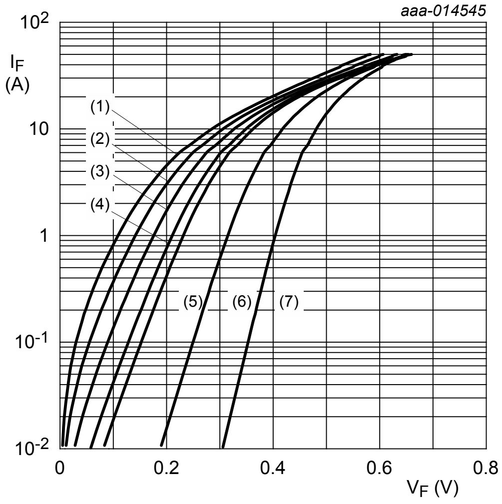
Ceramic PCB, Al_2O_3, standard footprint

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

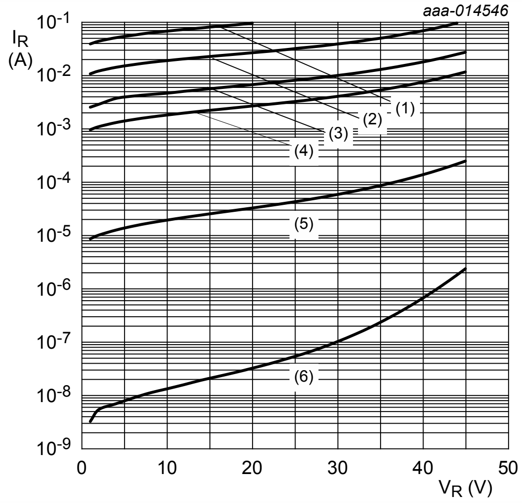
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{(BR)R}$	reverse breakdown voltage	I_R = 5 mA; T_j = 25 °C; $t_p \leq$ 1.2 ms; $\delta \leq$ 0.12; pulsed		45	-	-	V
V_F	forward voltage	I_F = 1 A; $t_p \leq$ 300 μs; $\delta \leq$ 0.02; T_j = 25 °C; pulsed		-	320	360	mV
		I_F = 2 A; $t_p \leq$ 300 μs; $\delta \leq$ 0.02; T_j = 25 °C; pulsed		-	340	-	mV
		I_F = 5 A; $t_p \leq$ 300 μs; $\delta \leq$ 0.02; T_j = 25 °C; pulsed		-	380	430	mV
		I_F = 10 A; $t_p \leq$ 300 μs; $\delta \leq$ 0.02; T_j = 25 °C; pulsed		-	420	490	mV
		I_F = 10 A; $t_p \leq$ 300 μs; $\delta \leq$ 0.02; T_j = 125 °C; pulsed		-	330	-	mV
I_R	reverse current	V_R = 5 V; $t_p \leq$ 3 ms; $\delta \leq$ 0.3; T_j = 25 °C; pulsed		-	15	-	μA
		V_R = 10 V; $t_p \leq$ 3 ms; $\delta \leq$ 0.3; T_j = 25 °C; pulsed		-	20	50	μA
		V_R = 30 V; $t_p \leq$ 3 ms; $\delta \leq$ 0.3; T_j = 25 °C; pulsed		-	60	-	μA
		V_R = 45 V; $t_p \leq$ 3 ms; $\delta \leq$ 0.3; T_j = 25 °C; pulsed		-	250	600	μA
C_d	diode capacitance	V_R = 1 V; f = 1 MHz; T_j = 25 °C		-	1190	-	pF
		V_R = 10 V; f = 1 MHz; T_j = 25 °C		-	400	-	pF
t_{rr}	reverse recovery time step recovery	I_F = 0.5 A; I_R = 0.5 A; $I_{R(meas)}$ = 0.1 A; T_j = 25 °C		-	37	-	ns
t_{rr}	reverse recovery time ramp recovery	dI_F/dt = 200 A/μs; T_j = 25 °C; I_F = 6 A; V_R = 26 V		-	17	-	ns
V_{FRM}	peak forward recovery voltage	I_F = 0.5 A; dI_F/dt = 20 A/μs; T_j = 25 °C		-	308	-	mV



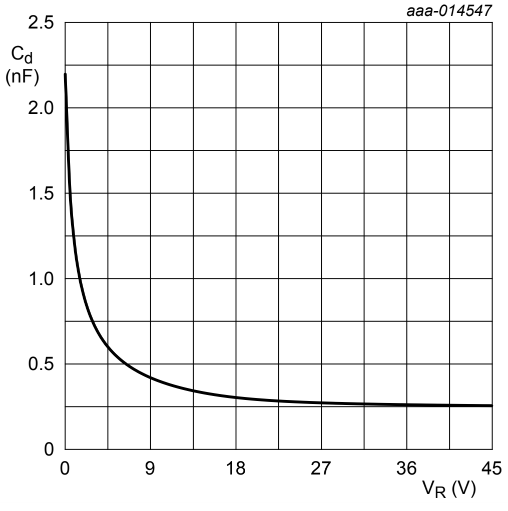
pulsed condition
(1) T_j = 175 °C
(2) T_j = 150 °C
(3) T_j = 125 °C
(4) T_j = 100 °C
(5) T_j = 85 °C
(6) T_j = 25 °C
(7) T_j = −40 °C

Fig. 4. Forward current as a function of forward voltage; typical values



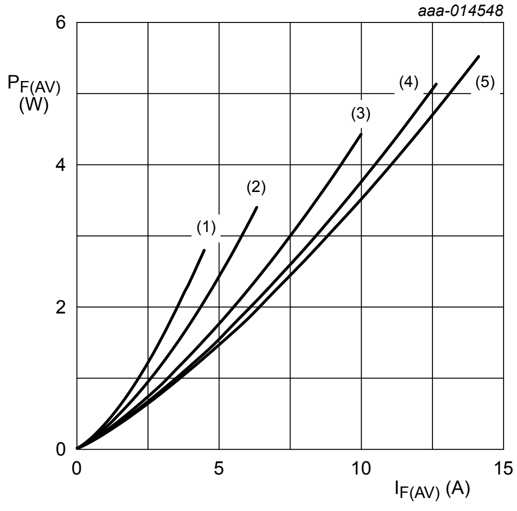
pulsed condition
(1) T_j = 150 °C
(2) T_j = 125 °C
(3) T_j = 100 °C
(4) T_j = 85 °C
(5) T_j = 25 °C
(6) T_j = −40 °C

Fig. 5. Reverse current as a function of reverse voltage; typical values



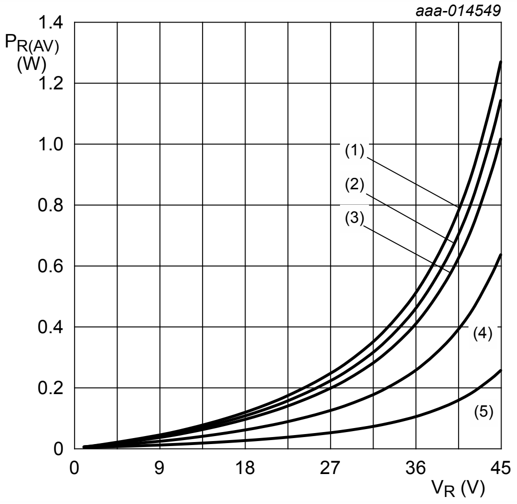
f = 1 MHz; T_{amb} = 25 °C

Fig. 6. Diode capacitance as a function of reverse voltage; typical values



T_j = 100 °C
(1) δ = 0.1
(2) δ = 0.2
(3) δ = 0.5
(4) δ = 0.8
(5) δ = 1

Fig. 7. Average forward power dissipation as a function of average forward current; typical values



T_j = 100 °C

(1) δ = 1

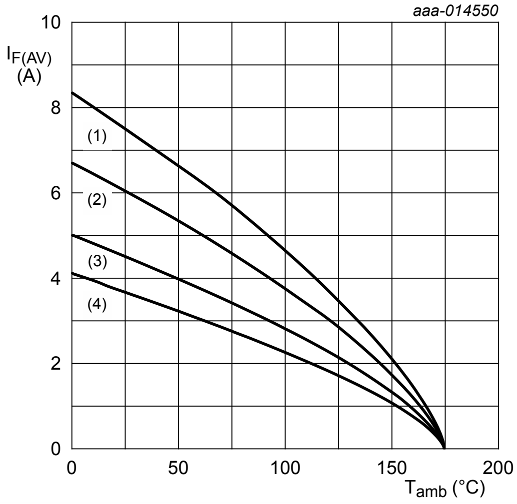
(2) δ = 0.9

(3) δ = 0.8

(4) δ = 0.5

(5) δ = 0.2

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T_j = 175 °C

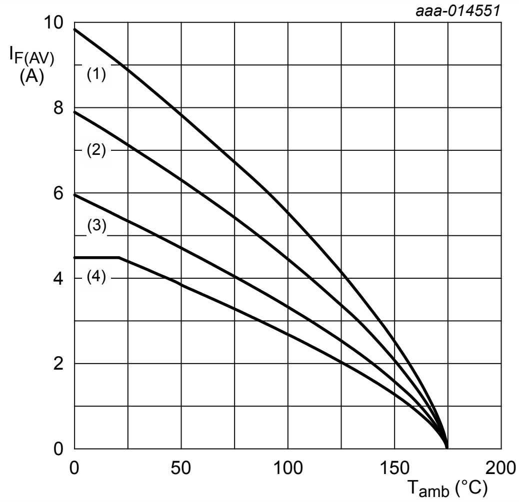
(1) δ = 1; DC

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 9. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm^2

T_j = 175 °C

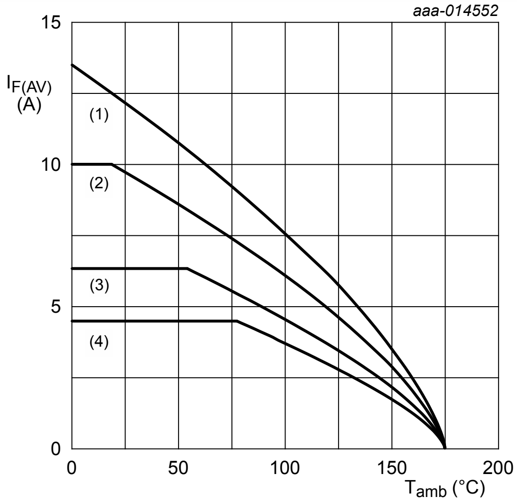
(1) δ = 1; DC

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al_2O_3, standard footprint

T_j = 175 °C

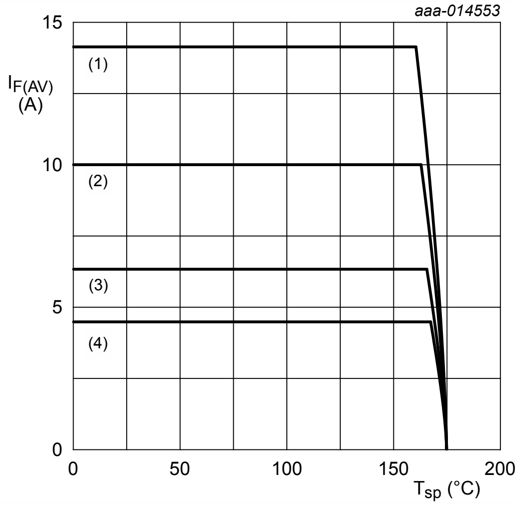
(1) δ = 1; DC

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values



T_j = 175 °C

(1) δ = 1; DC

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 12. Average forward current as a function of solder point temperature; typical values